

**Congratulations to the Twenty Three Newly Elected
IEEE Electron Devices Society Fellows
Effective January 1, 2016**

Eugenio Cantatore, Eindhoven University of Technology, Eindhoven, Netherlands
for contributions to the design of circuits with organic thin film transistors

Chorng-Ping Chang, Applied Materials, Inc., Santa Clara, CA, USA
for contributions to replacement gate and shallow trench isolation for CMOS technology

Gilles Dambrine, IEMN- Institute of Electronic, CNRS, France
for contributions to the modeling of small signal and noise characteristics in nanoscale high-frequency devices

Ananth Dodabalapur, University of Texas at Austin, Austin, TX, USA
for contributions to organic electronic devices and circuits

Ravindranath Droopad, Texas State University, San Marcos, TX, USA
for contributions to epitaxial growth of advanced materials for RF and CMOS applications

Mukta Farooq, IBM Corporation, Hopewell Jct, NY, USA
for contributions to 3D integration and interconnect technology

Patrick Fay, University of Notre Dame, Notre Dame, IN, USA
for contributions to compound semiconductor tunneling and high-speed device technologies

Patrick French, TU Delft- Delft University of Technology, Delft, Netherlands
for contributions to micro-electromechanical devices and systems

Tibor Grasser, Technische Universität Wien: TU Wien, Vienna, Austria
for contributions to modeling the reliability of semiconductor devices

Mark Hersam, Northwestern University, Evanston, IL, USA
for contributions to carbon nanomaterial processing methods and devices

Qing-An Huang, Southeast University, Nanjing, China
for contributions to modeling and packaging of microsensors and microactuators

Adrian Ionescu, EPFL - École polytechnique fédérale de Lausanne, Lausanne, Switzerland
for contributions to the development of novel devices for low power applications

Alvin Joseph, IBM Thomas J. Watson Research Center, Yorktown Heights, NY, USA
for contributions to silicon-germanium bipolar-CMOS and RF silicon-on-insulator technology

Jong Ho Lee, Seoul National University, Seoul, Korea
for contributions to development and characterization of bulk multiple gate field effect transistors

Victor Lubecke, University of Hawaii at Manoa, Honolulu, HI, USA
for leadership in the development of microwave transducers for biomedical application

Jian-Guo Ma, Tianjin University, Tianjin, China
for leadership in microwave electronics and RFIC applications

Souvik Mahapatra, IIT- Indian Institute of Technology Bombay, Mumbai, India
for contributions to CMOS transistor gate stack reliability

Sudip Mazumder, University of Illinois at Chicago, Chicago, IL, USA
for contributions to analysis and control of power electronics systems

Ellis Meng, University of Southern California, Los Angeles, CA, USA
for contributions to biomedical microelectromechanical systems

Ajay Poddar, Synergy Microwave Corporation, Paterson, NJ, USA
for contributions to microwave oscillators

Leonard Register, The University Of Texas At Austin, Austin, TX, USA
for contributions to modeling of charge transport in nanoscale CMOS devices

Akira Toriumi, University of Tokyo, Tokyo, Japan
for contributions to device physics and materials engineering for advanced CMOS technology

Ernest Wu, IBM Microelectronics- Avent, Inc., Essex Junction, VT, USA
for contributions to gate oxide reliability of CMOS devices

Guido.Groeseneken
2015 EDS Fellows Chair
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